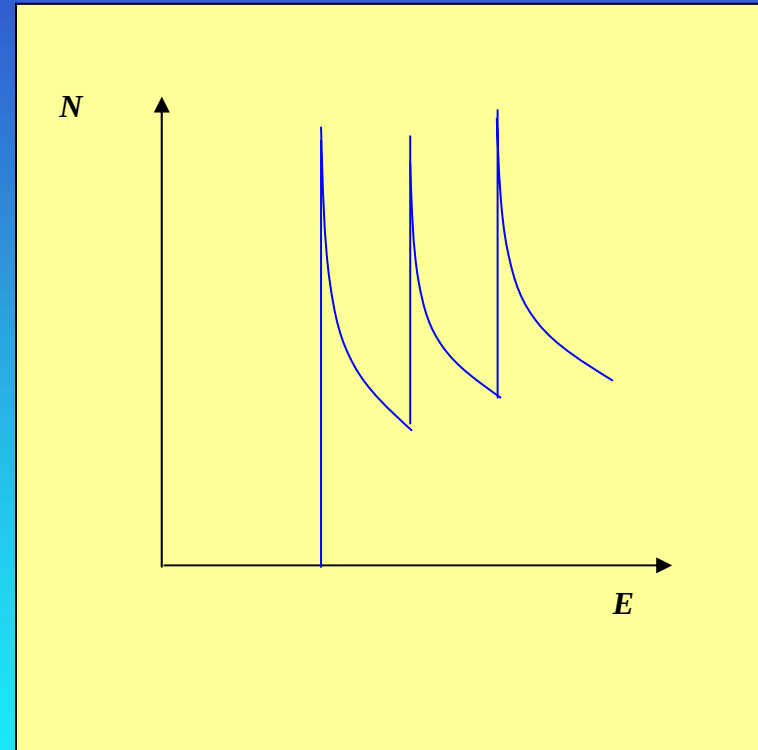


Quantum wire structures

$$E_n = \frac{\pi^2 \hbar^2 n_1^2}{2m^* a^2} + \frac{\pi^2 \hbar^2 n_2^2}{2m^* a^2} + \frac{\hbar^2 k_y^2}{2m^*}$$

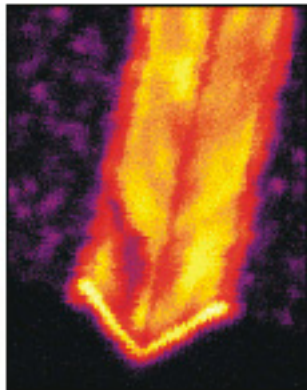
$$N(E)dE = \frac{1}{\pi} \left(\frac{2m^*}{\hbar^2} \right)^{1/2} E^{-1/2} dE$$

$$N(E) = \sum N(E)_{n_1, n_2} ; \quad N(E)_{n_1, n_2} = \frac{\sqrt{2m^*}}{\pi \hbar} \frac{\Theta(E - \varepsilon_{n_1, n_2})}{\sqrt{E - \varepsilon_{n_1, n_2}}}$$

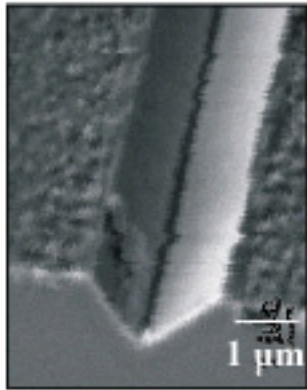
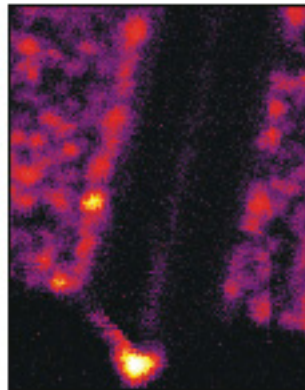


V-groove quantum wires

735 - 740 nm

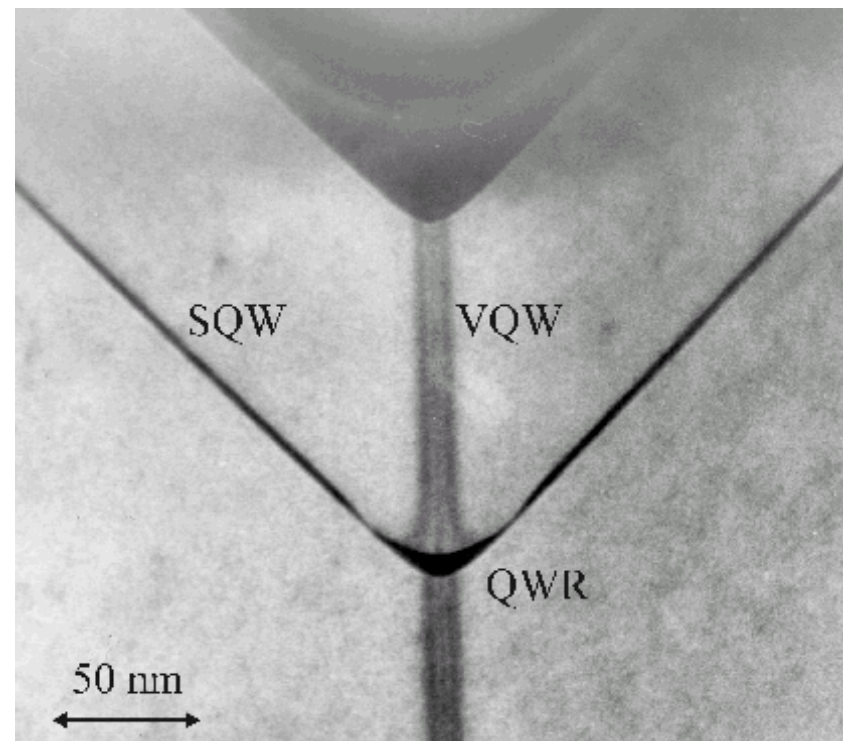
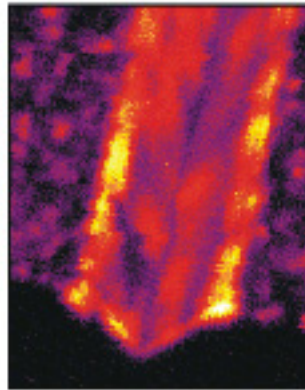


790 - 795 nm



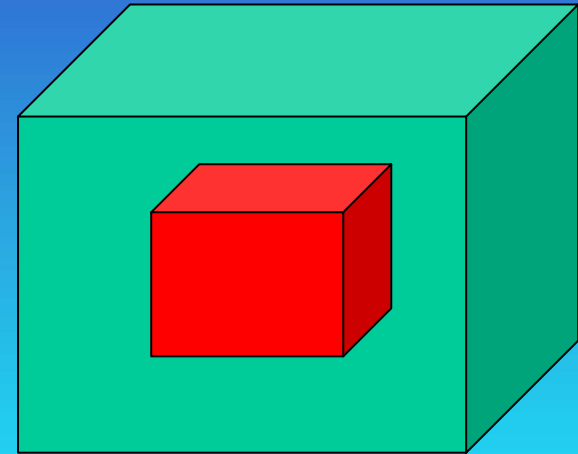
SEM

750 - 755 nm



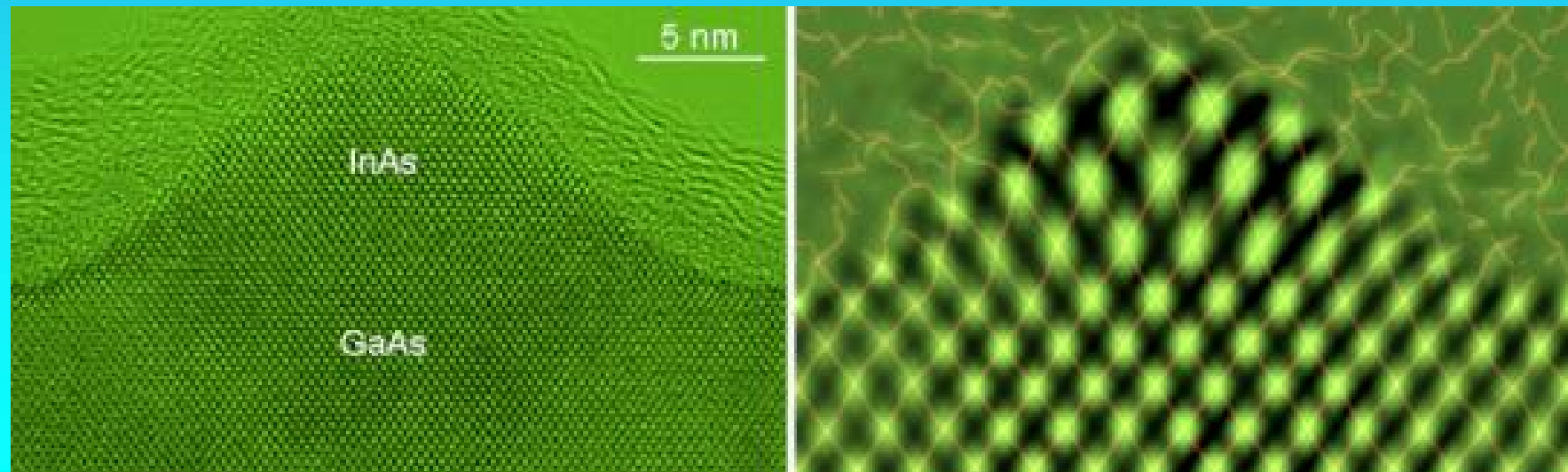
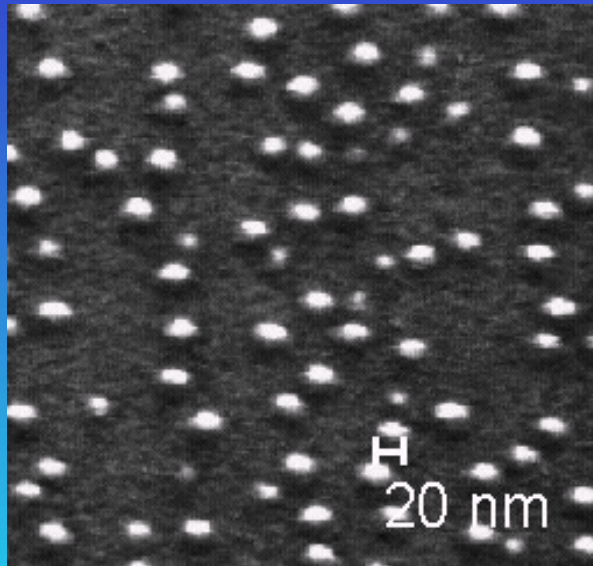
Quantum dots

$$E_n = \frac{\pi^2 \hbar^2 n_1^2}{2m^* a^2} + \frac{\pi^2 \hbar^2 n_2^2}{2m^* a^2} + \frac{\pi^2 \hbar^2 n_3^2}{2m^* a^2}$$

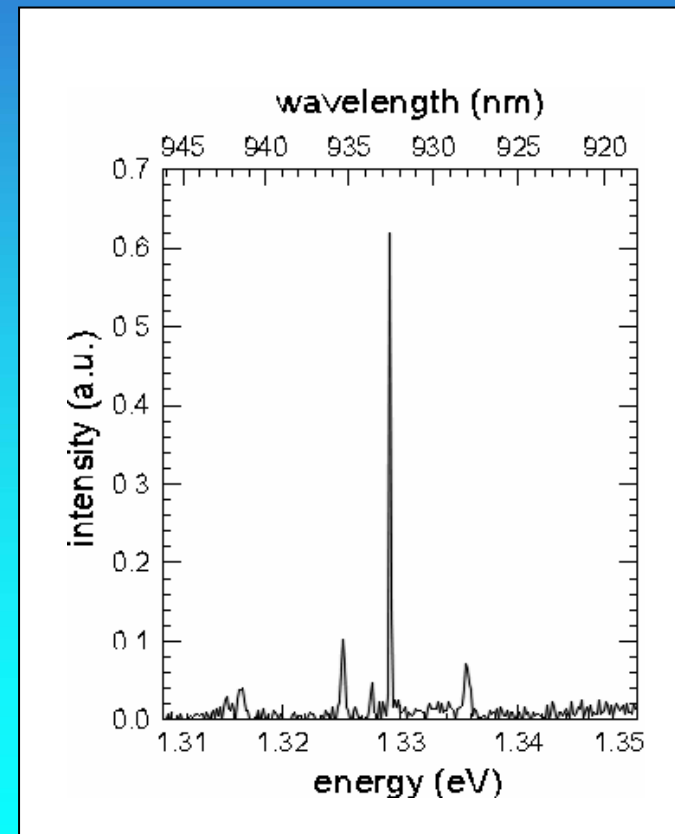
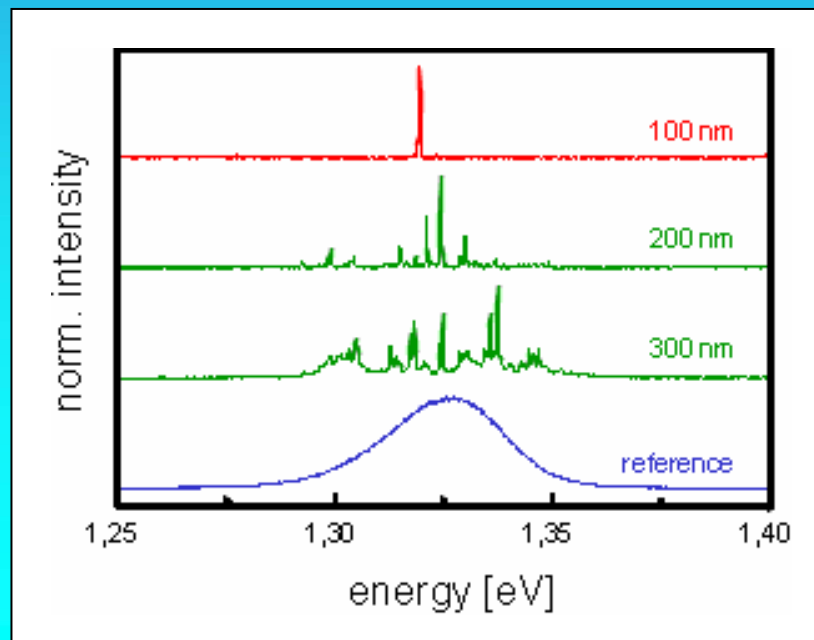
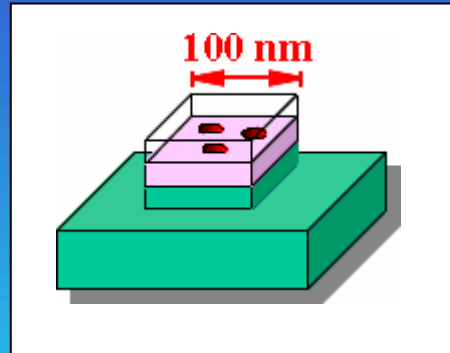


$$N(E) = \sum N(E)_{n_1 n_2 n_3} ; \quad N(E)_{n_1 n_2 n_3} = \delta(E - \varepsilon_{n_1 n_2 n_3})$$

InAs dots on GaAs



Spectroscopy of single InAs dots



Field effect transistors

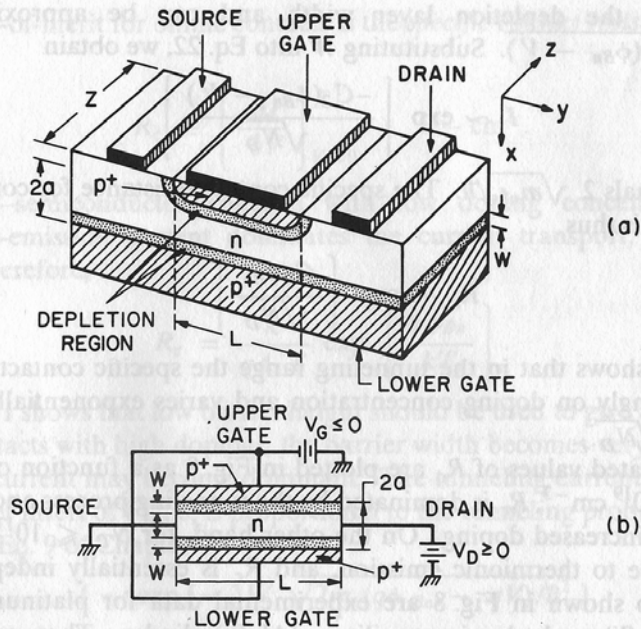


Fig. 9 (a) Perspective view of a JFET. (b) Cross section of the central region of a JFET. The source is grounded and the gate voltage and drain voltage are biased under normal operation conditions.

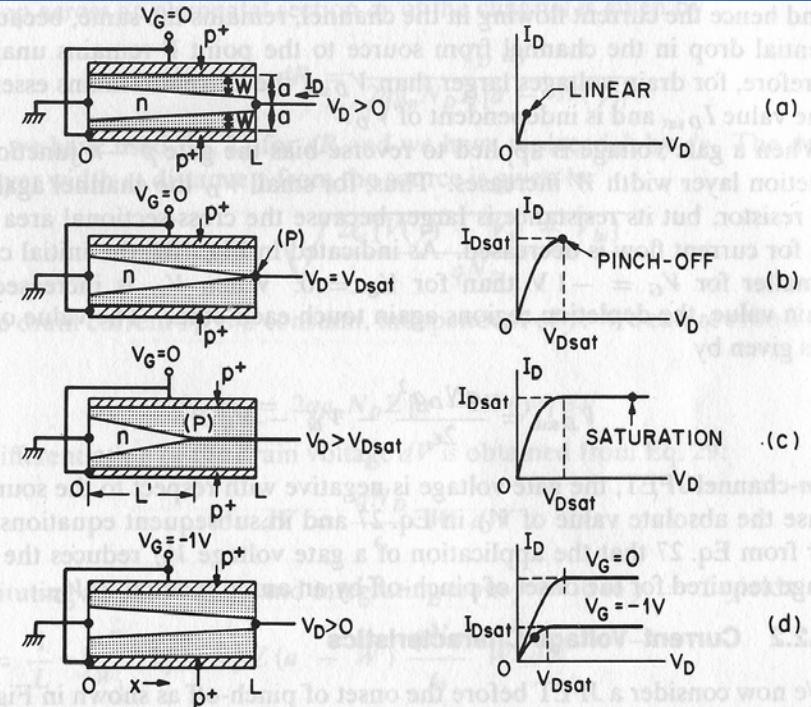
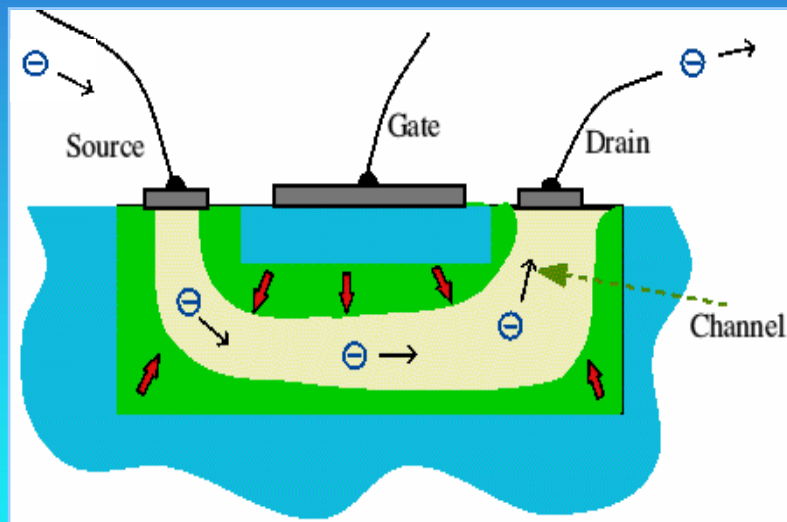
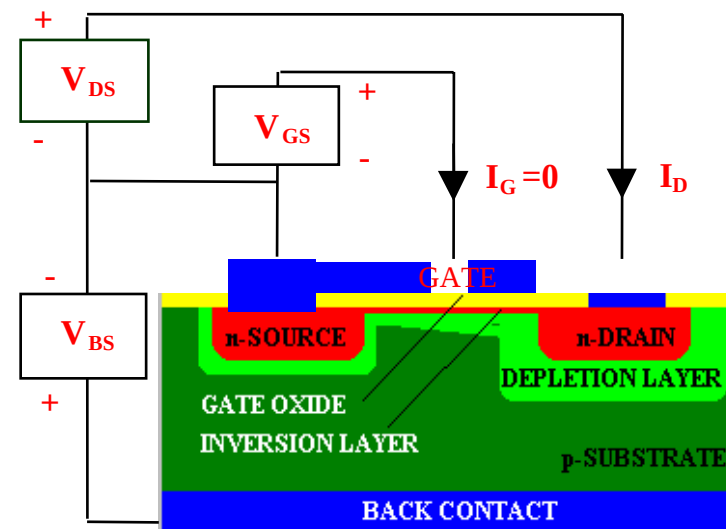


Fig. 10 Variation of depletion layer width and output characteristics of a JFET under various biasing conditions. (a) $V_G = 0$ and small V_D . (b) $V_G = 0$ and at pinch-off. (c) $V_G = 0$ and post pinch-off ($V_D > V_{Dsat}$). (d) $V_G = -1$ V and small V_D .

Field effect transistors

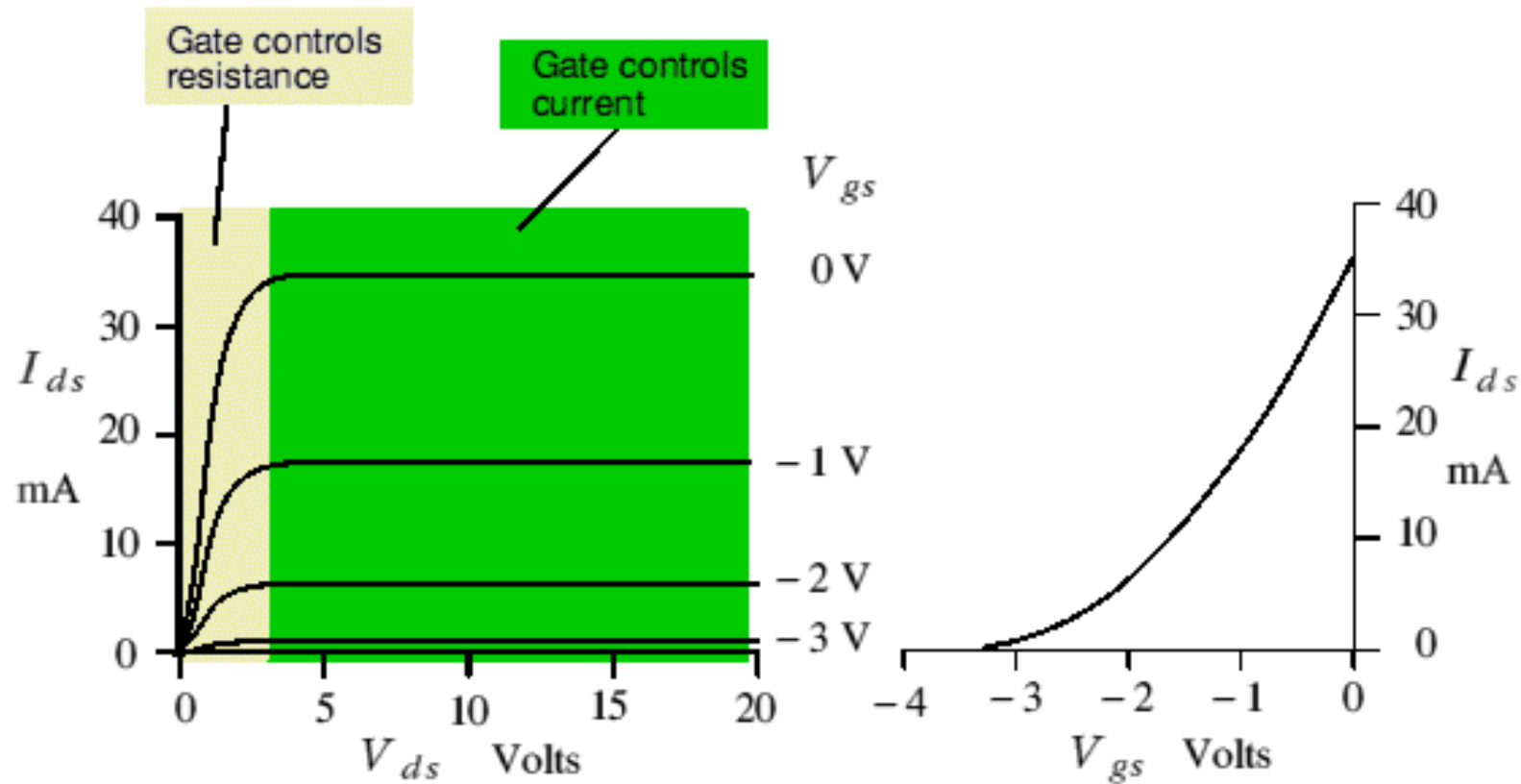


Junction Field Effect Transistor

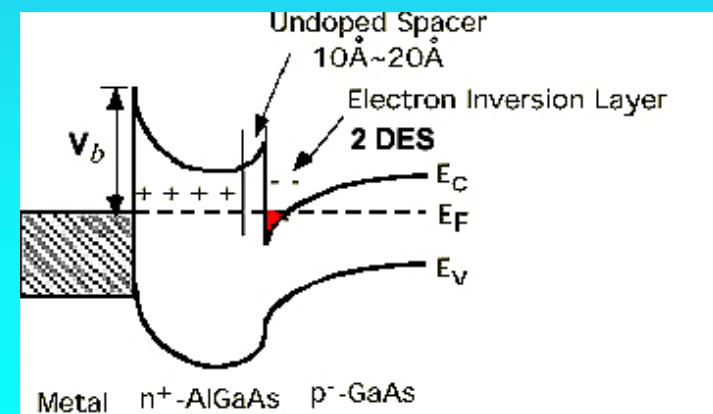
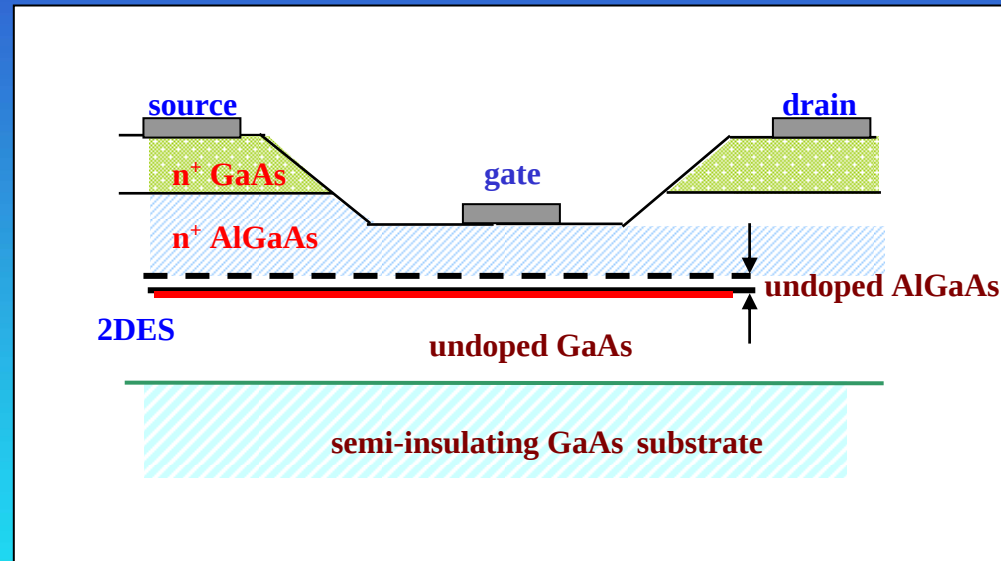


**Metal Oxide Semiconductor
Field Effect Transistor**

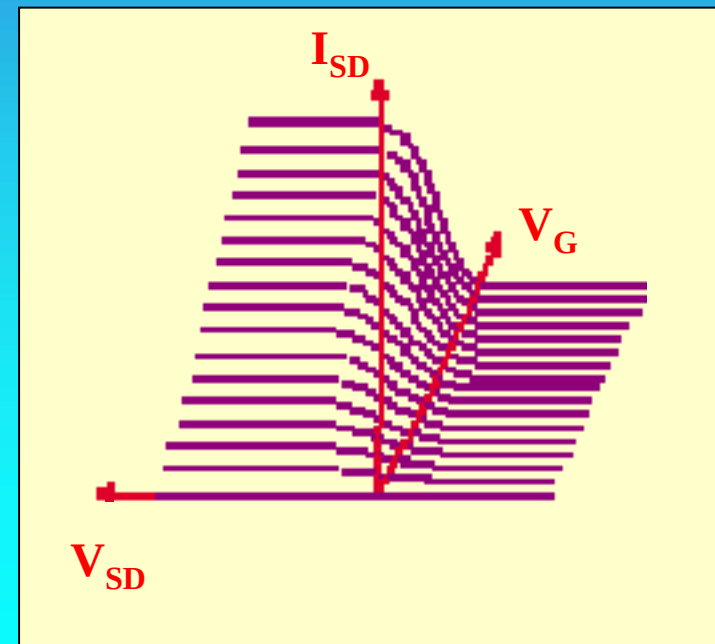
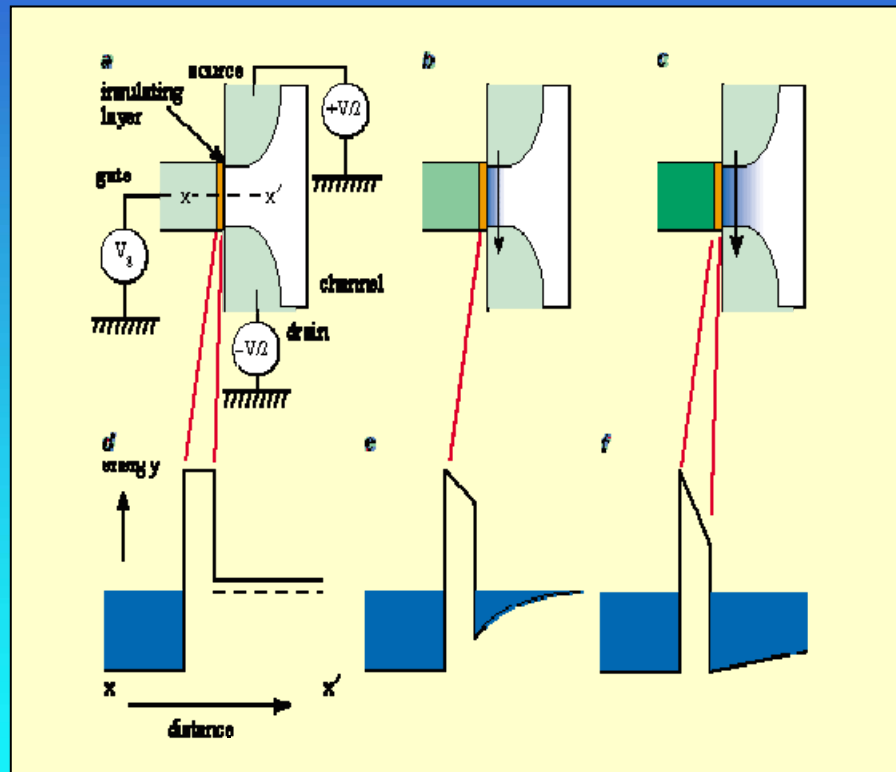
FET characteristics



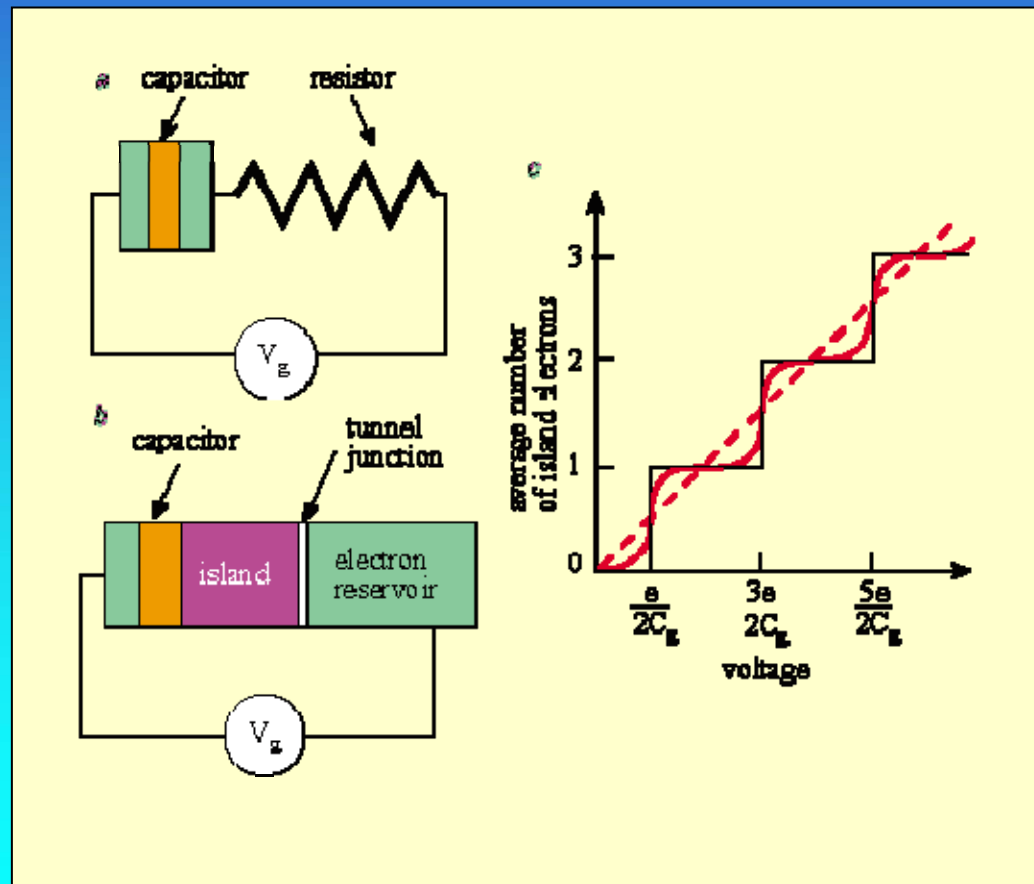
MODFET



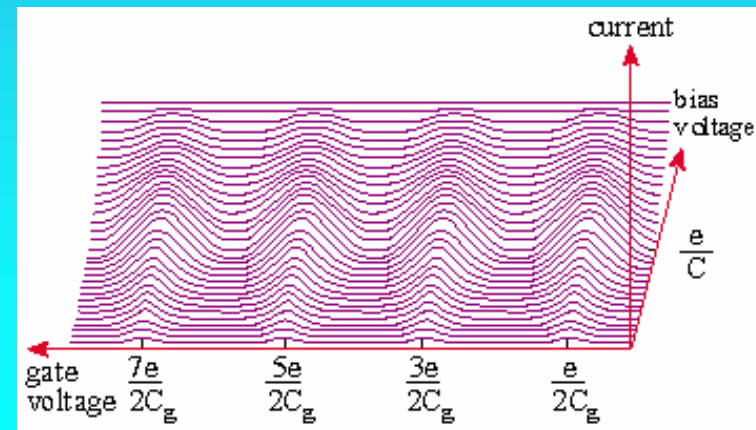
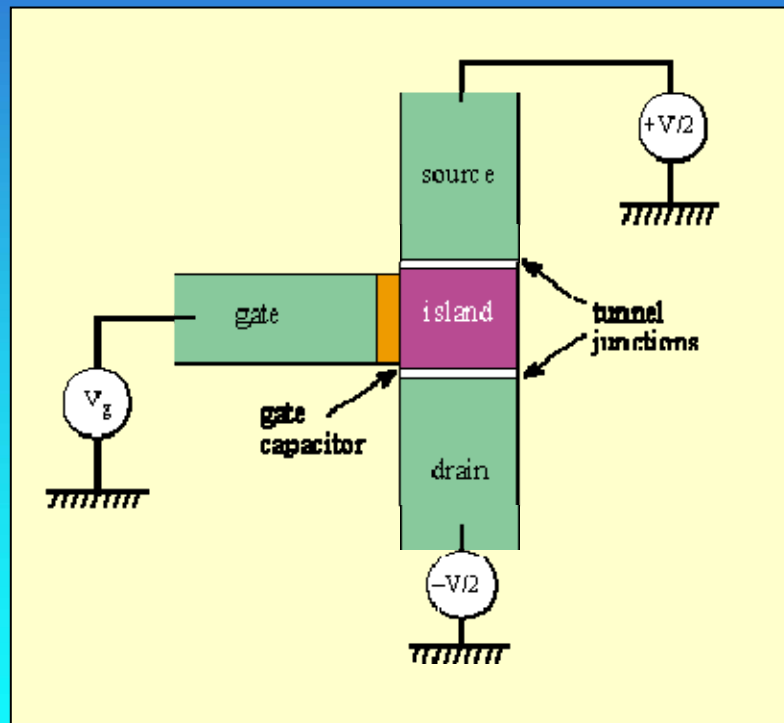
MOSFET



Single electron transistor



SET characteristics



SET scanning electrometer

